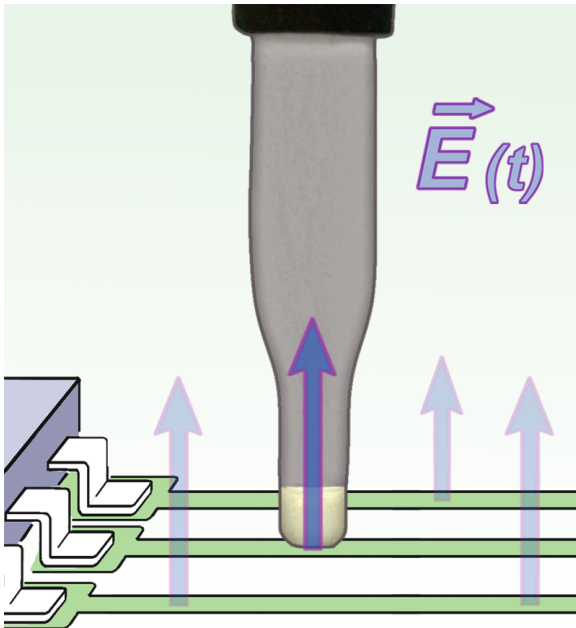


# XF-E 10

电场探头 (30MHz-6GHz)



## Short description

XF-E 10型电场探头底面的电极仅有约0.2mm宽，用于定位最小的电场，例如0.1mm宽的导线、高针数集成电路的单个引脚等发射的电场。测试时将该电场探头放置在受测物体上。

The XF-E 10 probe is a passive near-field probe. In principle it has the same structure as the XF-E 04 and XF-E 09 probes. The resolution of XF-E 10, however, is significantly higher. Normally the probe head is positioned directly onto the measured object (high electric field strength). It is not suitable for measurements from greater distances, which can be done using the XF-E 04 or XF-E 09. The near-field probe is small and handy. It has a current attenuating sheath and, therefore, is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50  $\Omega$  input. The H-field probe has an internal terminating resistance.

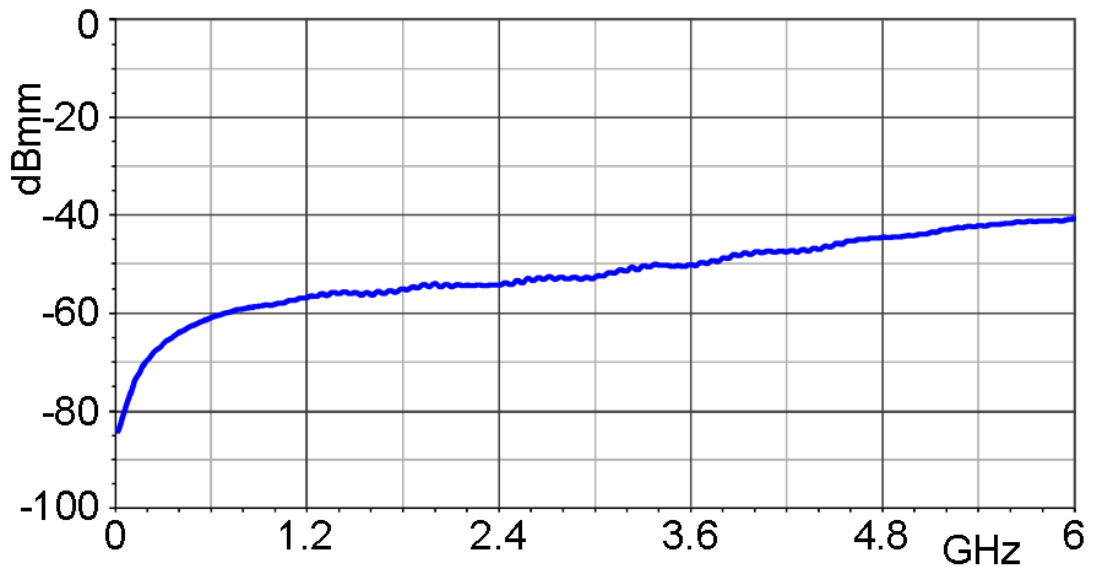
## Technical parameters

|      |                             |
|------|-----------------------------|
| 频率范围 | 30 MHz ... 6 GHz            |
| 分辨率  | $\approx 0.2$ mm            |
| 探头尺寸 | $\approx (0.5 \times 2)$ mm |
| 输出接口 | SMA, female, jack           |
| 重量   | 15 g                        |

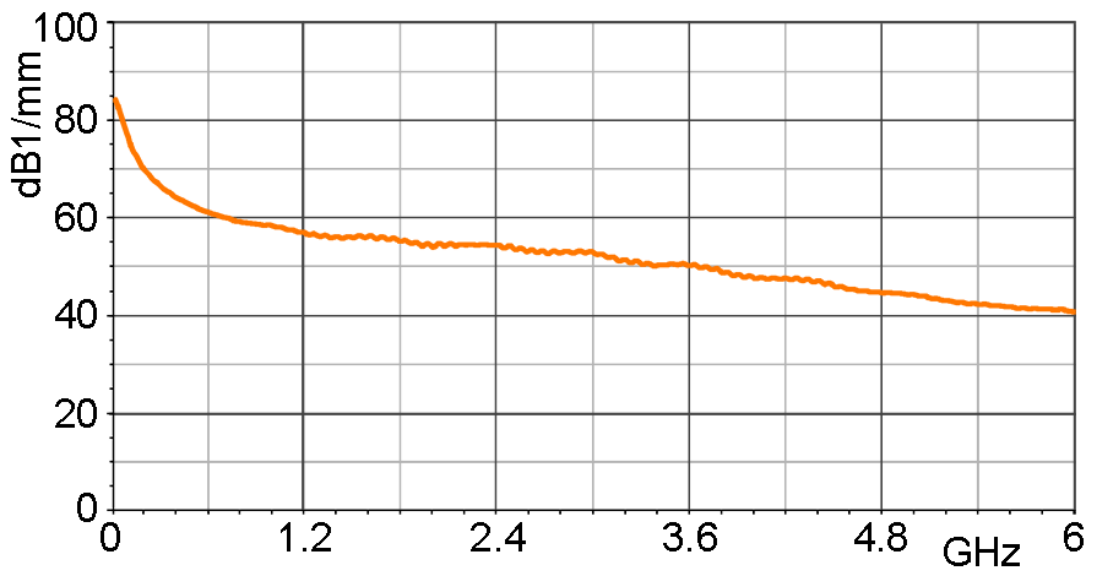
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频率特性 [dB $\mu$ V] / [dB $\mu$ V/mm]

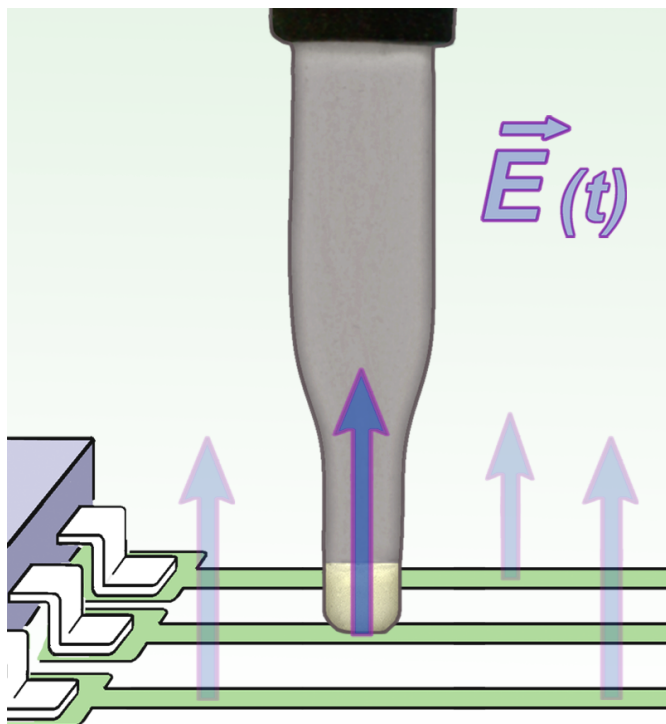


电场校正曲线 [dB $\mu$ V/mm] / [dB $\mu$ V]



# XF-E 10

电场探头 (30MHz-6GHz)



Probe head

